



S8550

TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM} : 0.625 \text{ W (} T_{amb}=25^{\circ}\text{C)}$$

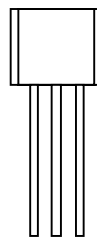
Collector current

$$I_{CM} : -0.5 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -40 \text{ V}$$

TO-92



1. EMITTER
2. BASE
3. COLLECTOR

1 2 3

ELECTRICAL CHARACTERISTICS($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100 \mu\text{A}$, $I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1 \text{ mA}$, $I_B=0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100 \mu\text{A}$, $I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40 \text{ V}$, $I_E=0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=20 \text{ V}$, $I_B=0$			-0.2	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-3 \text{ V}$, $I_C=0$			-0.1	μA
DC current gain(note)	$H_{FE(1)}$	$V_{CE}=1 \text{ V}$, $I_C=50 \text{ mA}$	85		300	
	$H_{FE(2)}$	$V_{CE}=1 \text{ V}$, $I_C=500 \text{ mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500 \text{ mA}$, $I_B=50 \text{ mA}$			-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500 \text{ mA}$, $I_B=50 \text{ mA}$			-1.2	V
Base-emitter voltage	V_{BE}	$I_E=100 \text{ mA}$			-1.4	V
Transition frequency	f_T	$V_{CE}=6 \text{ V}$, $I_C=20 \text{ mA}$ $f=30 \text{ MHz}$	150			MHz

CLASSIFICATION OF $H_{FE(1)}$

Rank	B	C	D
Range	85-160	120-200	160-300